

creating a plasma from the etchant gas in the etch chamber;

etching away parts of the metal-containing layer not disposed below the etch mask, wherein some of the etched away parts of the metal-containing layer is redeposited to form residual sidewall passivation while the substrate is in the etch chamber;

discontinuing the flow of the etchant gas into the etch chamber;

flowing an etch mask stripping gas into the etch chamber;

creating a plasma from the etch mask stripping gas in the etch chamber;

stripping away the etch mask and removing [some] most of the residual sidewall passivation, while the substrate is in the etch chamber, wherein plasma created by the etch mask stripping gas strips away the etch mask and removes most of the residual sidewall passivation;  
and

removing the substrate from the etch chamber.

15. (Once Amended) A method for etching at least partially through a metal-containing layer disposed above a substrate, wherein part of said metal-containing layer is disposed below an etch mask and part of said metal-containing layer is not disposed below the etch mask, comprising the steps of:

placing the substrate in the etch chamber;

etching away parts of the metal-containing layer not disposed below the etch mask, wherein some of the etched away parts of the metal-containing layer is redeposited to form residual sidewall passivation on the substrate, while the substrate is in the etch chamber;

using a stripping gas to strip [stripping] away the etch mask and [removing some] remove most of the sidewall passivation while the substrate is in the etch chamber; and

removing the substrate from the etch chamber.